Unit: mm

TOSHIBA Transistor Silicon NPN Triple Diffused Type (PCT Process)

2SC2229

Black and White TV Video Output Applications High-Voltage Switching Applications Driver Stage Audio Amplifier Applications

- High breakdown voltage: VCEO = 150 V (min)
- Low output capacitance: Cob = 5.0 pF (max)
- High transition frequency: fT = 120 MHz (typ.)

Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V _{CBO}	200	V	
Collector-emitter voltage	V _{CEO}	150	V	
Emitter-base voltage	V _{EBO}	5	V	
Collector current	I _C	50	mA	
Base current	lΒ	20	mA	
Collector power dissipation	PC	800	mW	
Junction temperature	Tj	150	°C	
Storage temperature range	T _{stg}	-55 to 150	°C	

0.75MAX. 1.0MAX. 0.6MAX. 1.27 1.27 1.27 1.27 1.27 1.27 1.27 1.27

EMITTER
 COLLECTOR
 BASE

JEDEC	TO-92MOD		
JEITA	_		
TOSHIBA	2-5J1A		

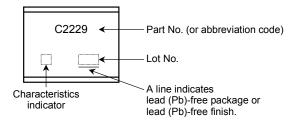
Weight: 0.36 g (typ.)

Electrical Characteristics (Ta = 25°C)

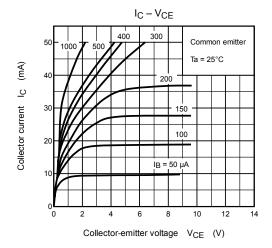
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	V _{CB} = 200 V, I _E = 0	_	_	0.1	μΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 5 V, I _C = 0	_	_	0.1	μA
DC current gain	h _{FE} (Note)	V _{CE} = 5 V, I _C = 10 mA	70	_	240	
Collector-emitter saturation voltage	V _{CE (sat)}	I _C = 10 mA, I _B = 1 mA	_	_	0.5	V
Base-emitter saturation voltage	V _{BE (sat)}	I _C = 10 mA, I _B = 1 mA	_	_	1	V
Transition frequency	f _T	V _{CE} = 30 V, I _C = 10 mA	_	120	_	MHz
Collector output capacitance	C _{ob}	V _{CB} = 10 V, I _E = 0, f = 1 MHz	_	3.5	5	pF

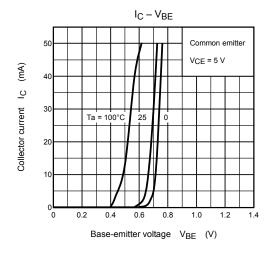
Note: hFE classification O: 70 to 140, Y: 120 to 240

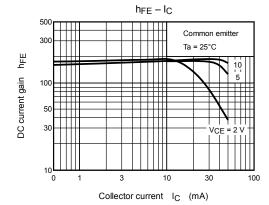
Marking

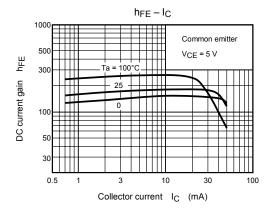


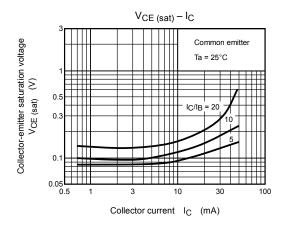
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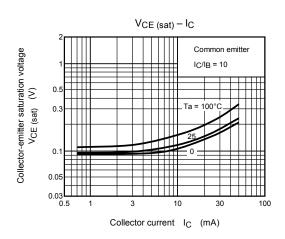


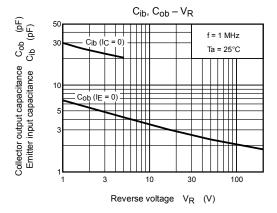


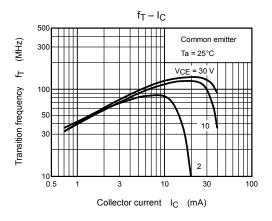


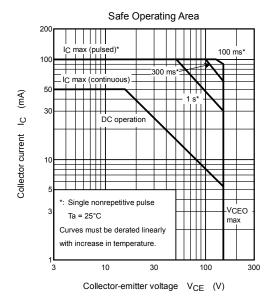


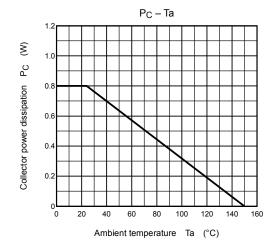












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